

AMENDMENTS TO THE CLAIMS:

The following listing of claims will replace all prior versions, and listings, of claims in the above-identified patent application.

LISTING OF THE CLAIMS:

1. (currently amended) A magnetoelectronics information device, comprising:
a free magnetic region;
a pinned magnetic region; and
a tunneling barrier interposed between said free magnetic region and said pinned magnetic region,

wherein magnetic moments of said free magnetic region and said pinned magnetic region that are adjacent to said tunneling barrier are oriented to provide a first magnetization state when:

a first magnetic field with a first field magnitude is produced in proximity to the magnetoelectronics information device at a first time (t_1);

a second magnetic field with a second field magnitude is produced in proximity to the magnetoelectronics information device at a second time (t_2);

said first magnetic field is adjusted to provide a third field magnitude that is less than said first field magnitude and greater than zero at a third time (t_3); and

said second magnetic field is adjusted to provide a fourth field magnitude that is less than said second field magnitude at a fourth time (t_4); and

said first magnetic field is adjusted to provide a fifth field magnitude that is less than said third field magnitude at a fifth time (t_5),

wherein $t_1 < t_3 < t_5$.

2. (currently amended) The magnetoelectronics information device of Claim 1,
wherein $t_1 < t_2 < t_3 < t_4 \leq t_5$.

3. (canceled)

4. (currently amended) The magnetoelectronics information device of Claim 13, wherein said fifth field magnitude is approximately zero.

5. (original) The magnetoelectronics information device of Claim 1, wherein said magnetic moment of said free magnetic region is preferably unbalanced.

6. (original) The magnetoelectronics information device of Claim 5, wherein shall mean that the fractional balance ratio (M_{br}) is in the range of about five hundredths (0.05) to about one tenth (0.1).

7. (currently amended) The magnetoelectronics information device of Claim 1, wherein said magnetic moments of said free magnetic region and said pinned magnetic region that are adjacent to said tunneling barrier are oriented to provide a second magnetization state when:

a third magnetic field with a fifth sixth field magnitude is produced in proximity to the magnetoelectronics information device at a fifth sixth time (t_5t_6)

a fourth magnetic field with said sixth seventh magnitude is produced in proximity to the magnetoelectronics information device at a sixth a seventh time (t_6t_7);

said third magnetic field is adjusted to provide an eighth seventh field magnitude that is less than said sixth fifth magnitude at an eighth seventh time (t_7t_8); and

said fourth magnetic field is adjusted to provide an eighth a ninth field magnitude that is less than said sixth seventh magnitude at an eighth a ninth time (t_8t_9).

8. (currently amended) The magnetoelectronics information device of Claim 7, wherein $t_4 < t_5 < t_6 < t_7 < t_8 \leq t_9$.

9. (currently amended) The magnetoelectronics information device of Claim 7, wherein $t_{45} < t_{67} < t_{56} < t_{89} < t_{78}$.

10. (currently amended) The magnetoelectronics information device of Claim 1, wherein said magnetic moments of said free magnetic region and said pinned magnetic region that are adjacent to said tunneling barrier are oriented to provide a second magnetization state when:

a third magnetic field with a ~~fifth-sixth~~ field magnitude is produced in proximity to the magnetoelectronics information device at a ~~fifth-sixth~~ time ($t_5 t_6$);

a fourth magnetic field with ~~said sixth~~ ~~seventh~~ field magnitude is produced in proximity to the magnetoelectronics information device at a ~~sixth~~~~seventh~~ time ($t_6 t_7$);

said third magnetic field is adjusted to provide ~~a seventh field~~~~an eighth~~ magnitude that is less than said ~~fifth-sixth~~ magnitude at ~~a seventh~~~~an eighth~~ time ($t_7 t_8$);

said fourth magnetic field is adjusted to provide ~~an eighth~~~~a ninth~~ field magnitude that is less than said ~~sixth~~~~seventh~~ magnitude and greater than zero at ~~an eighth~~~~a ninth~~ time ($t_8 t_9$); and

said fourth magnetic field is adjusted to provide a ~~ninth~~~~tenth~~ field magnitude that is less than said ~~eighth~~~~ninth~~ field magnitude at a ~~ninth~~~~tenth~~ time ($t_9 t_{10}$).

11. (currently amended) The magnetoelectronics information device of Claim 10, wherein $t_4 < t_5 < t_6 < t_7 < t_8 < t_9 \leq t_{10}$.

12. (original) The magnetoelectronics information device of Claim 10, wherein said ninth field magnitude is approximately zero.

13. (original) The magnetoelectronics information device of Claim 1, wherein said free magnetic region comprises:

a first ferromagnetic layer;

a second ferromagnetic layer; and

a non-magnetic layer interposed between said first ferromagnetic layer and said second ferromagnetic layer.

14. (original) The magnetoelectronics information device of Claim 13, wherein said first ferromagnetic layer is at least partially formed of one material selected from the group comprising nickel (Ni), iron (Fe), or cobalt (Co).

15. (original) The magnetoelectronics information device of Claim 14, wherein said second ferromagnetic layer is at least partially formed of one material selected from the group comprising nickel (Ni), iron (Fe), or cobalt (Co).

16. (original) The magnetoelectronics information device of Claim 1, wherein said non-magnetic layer is at least partially formed of one material selected from the group ruthenium (Ru), osmium (Os), rhenium (Re), chromium (Cr), rhodium (Rh), or copper (Cu).

17. (original) The magnetoelectronics information device of Claim 1, wherein said pinned magnetic region comprises an anti-ferromagnetic layer adjacent to a ferromagnetic layer.

18. (original) The magnetoelectronics information device of Claim 17, wherein said anti-ferromagnetic layer is at least partially formed of one material selected from the group comprising iridium manganese iridium manganese (IrMn), iron manganese (FeMn), rhodium manganese (RhMn), platinum manganese (PtMn), and platinum palladium manganese (PtPdMn)

19. (original) The magnetoelectronics information device of Claim 1, wherein said magnetoelectronics information device is an MRAM element.

20. (original) The magnetoelectronics information device of Claim 1, wherein said third field magnitude is less than about seventy-five percent (75%) of the first field magnitude and greater than about twenty five percent (25%) of the first field magnitude.

21. (original) The magnetoelectronics information device of Claim 1, wherein said third field magnitude is about fifty percent (50%) of the first field magnitude.

22. (currently amended) In a magnetoelectronics information device having a free magnetic region, a pinned magnetic region and a tunneling barrier interposed between said free magnetic region and said pinned magnetic region, a method for writing the magnetoelectronics information device comprising the steps of:

producing a first magnetic field with a first field magnitude in proximity to the magnetoelectronics information device at a first time (t_1);

producing a second magnetic field with a second field magnitude in proximity to the magnetoelectronics information device at a second time (t_2);

adjusting said first magnetic field to provide a third field magnitude at a third time (t_3) that is less than said first field magnitude and greater than zero; and

adjusting said second magnetic field to provide a fourth field magnitude at a fourth time (t_4) that is less than said second magnitude;

adjusting said first magnetic field to provide a fifth field magnitude that is less than said third field magnitude at a fifth time (t_5),

wherein $t_1 < t_3 < t_5$.

23. (currently amended) The method for writing the magnetoelectronics information device of Claim 22, wherein $t_1 < t_2 < t_3 < t_4 \leq t_5$.

24. (canceled)

25. (currently amended) The method for writing the magnetoelectronics information device of Claim 2422, wherein said fifth magnitude is approximately zero.

26. (currently amended) The method for writing the magnetoelectronics information device of Claim 22, further comprising the steps of:

adjusting a third magnetic field to provide a ~~fifthsixth~~ field magnitude in proximity to the magnetoelectronics information device at a ~~fifthsixth~~ time (~~t₅t₆~~);

adjusting a fourth magnetic field to provide a ~~sixthseventh~~ field magnitude in proximity to the magnetoelectronics information device at a ~~sixthseventh~~ time (~~t₆t₇~~);

adjusting said third magnetic field to provide a ~~a-seventhan eighth~~ field magnitude that is less than said ~~fifthsixth~~ field magnitude at a ~~a-seventhan eighth~~ time (~~t₇t₈~~); and

adjusting said fourth magnetic field to provide a ~~an-eightha ninth~~ field magnitude that is less than said ~~sixthseventh~~ field magnitude at a ~~an-eightha ninth~~ time (~~t₈t₉~~).

27. (currently amended) The method for writing the magnetoelectronics information device of Claim 26, wherein $t_4 < t_5 < t_6 < t_7 < t_8 \leq t_9$.

28. (currently amended) The method for writing the magnetoelectronics information device of Claim 26, wherein $t_{45} < t_{67} < t_{56} < t_{89} < t_{78}$.

29. (currently amended) The method for writing the magnetoelectronics information device of Claim 22, further comprising the steps of:

adjusting a third magnetic field to provide a ~~fifthsixth~~ field magnitude in proximity to the magnetoelectronics information device at a ~~fifthsixth~~ time (~~t₅t₆~~);

adjusting a fourth magnetic field to provide a ~~sixthseventh~~ field magnitude in proximity to the magnetoelectronics information device at a ~~sixthseventh~~ time at a ~~sixth~~ time (~~t₆t₇~~);

adjusting said third magnetic field to provide a ~~a-seventh field an eighth~~ magnetic field that is less than said ~~fifthsixth~~ field magnitude at a ~~a-seventhan eighth~~ time (~~t₇t₈~~);

adjusting said fourth magnetic field to provide a ~~an-eightha ninth~~ field magnitude that is less than said ~~sixthseventh~~ field magnitude and greater than zero at a ~~an ninth~~ time (~~t₈t₉~~); and

adjusting said fourth magnetic field to provide a ~~ninthtenths~~ field magnitude that is less than said ~~eighthninth~~ field magnitude at a ~~ninthtenths~~ time (~~t₉t₁₀~~).

30. (currently amended) The magnetoelectronics information device of Claim 29, wherein $t_4 < t_5 < t_6 < t_7 < t_8 < t_9 \leq t_{10}$.

31. (currently amended) The magnetoelectronics information device of Claim 29, wherein said ninthtenth field magnitude is approximately zero.

32. (original) The magnetoelectronics information device of Claim 22, wherein said magnetoelectronics information device is an MRAM element.

33. (original) The magnetoelectronics information device of Claim 22, wherein said third field magnitude is less than about seventy-five percent (75%) of the first field magnitude and greater than about twenty five percent (25%) of the first field magnitude.

34. (original) The magnetoelectronics information device of Claim 22, wherein said third field magnitude is about fifty percent (50%) of the first field magnitude.

35. (currently amended) A MRAM element, comprising:

a free magnetic region comprising a first ferromagnetic layer, a second ferromagnetic layer and a non-magnetic layer interposed between said first ferromagnetic layer and said second ferromagnetic layer;

a pinned magnetic region magnetically coupled to said free magnetic region, said pinned magnetic region comprising a third ferromagnetic layer and an anti-ferromagnetic layer; and

a tunneling barrier interposed between said free magnetic region and said pinned magnetic region,

wherein a magnetic moment of said free magnetic region is unbalanced and magnetic moments of said free magnetic region and said pinned magnetic region that are adjacent to said tunneling barrier are oriented to provide a first magnetization state when:

a first magnetic field with a first field magnitude is produced in proximity to the MRAM element at a first time (t_1);

a second magnetic field with a second field magnitude is produced in proximity to the MRAM element at a second time (t_2);

 said first magnetic field is adjusted to provide a third field magnitude that is less than said first field magnitude and greater than zero at a third time (t_3); and

 said second magnetic field is adjusted to provide a fourth field magnitude that is less than said second field magnitude at a fourth time (t_4);

said first magnetic field is adjusted to provide a fifth field magnitude that is less than said third field magnitude at a fifth time (t_5),

wherein $t_1 < t_3 < t_5$.